

3.3-V RS-485 TRANSCEIVERS

FEATURES

- Operates With a 3.3-V Supply
- Bus-Pin ESD Protection Exceeds 16 kV HBM
- 1/8 Unit-Load Option Available (Up to 256 Nodes on the Bus)
- Optional Driver Output Transition Times for Signaling Rates ⁽¹⁾ of 1 Mbps, 10 Mbps, and 32 Mbps
- Meets or Exceeds the Requirements of ANSI TIA/EIA-485-A
- Bus-Pin Short Circuit Protection From -7 V to 12 V
- Low-Current Standby Mode . . . 1 μ A Typical
- Open-Circuit, Idle-Bus, and Shorted-Bus Failsafe Receiver
- Thermal Shutdown Protection
- Glitch-Free Power-Up and Power-Down Protection for Hot-Plugging Applications

APPLICATIONS

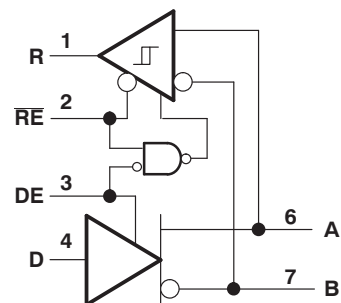
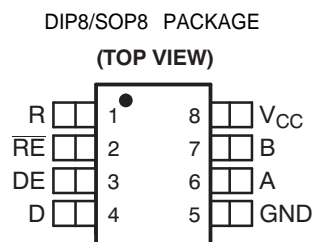
- Digital Motor Control
- Utility Meters
- Chassis-to-Chassis Interconnects
- Electronic Security Stations
- Industrial Process Control
- Building Automation
- Point-of-Sale (POS) Terminals and Networks

(1) The signaling rate of a line is the number of voltage transitions that are made per second expressed in the units bps (bits per second).

DESCRIPTION

The SN65HVD10, SN65HVD11, and SN65HVD12, combine a 3-state differential line driver and differential input line receiver that operate with a single 3.3-V power supply. They are designed for balanced transmission lines and meet or exceed ANSI standard TIA/EIA-485-A and ISO 8482:1993. These differential bus transceivers are monolithic integrated circuits designed for bidirectional data communication on multipoint bus-transmission lines. The drivers and receivers have active-high and active-low enables respectively, that can be externally connected together to function as direction control. Very low device standby supply current can be achieved by disabling the driver and the receiver.

The driver differential outputs and receiver differential inputs connect internally to form a differential input/output (I/O) bus port that is designed to offer minimum loading to the bus whenever the driver is disabled or $V_{CC} = 0$. These parts feature wide positive and negative common-mode voltage ranges, making them suitable for party-line applications.



ORDERING INFORMATION

DEVICE	Package Type	MARKING	Packing	Packing Qty
SN65HVD10EIN	DIP8L	65HVD10	TUBE	2000pcs/box
SN65HVD11EIN	DIP8L	65HVD11	TUBE	2000pcs/box
SN65HVD12EIN	DIP8L	65HVD12	TUBE	2000pcs/box
SN65HVD10EIM/TR	SOP8L	65HVD10	REEL	2500pcs/reel
SN65HVD11EIM/TR	SOP8L	65HVD11	REEL	2500pcs/reel
SN65HVD12EIM/TR	SOP8L	65HVD12	REEL	2500pcs/reel

ABSOLUTE MAXIMUM RATINGS

 over operating free-air temperature range unless otherwise noted ⁽¹⁾ ⁽²⁾

		UNIT	
V_{CC}	Supply voltage range	-0.3 V to 6 V	
	Voltage range at A or B	-9 V to 14 V	
	Input voltage range at D, DE, R or \overline{RE}	-0.5 V to $V_{CC} + 0.5$ V	
	Voltage input range, transient pulse, A and B, through 100 Ω , see Figure 11	-50 V to 50 V	
I_O	Receiver output current	-11 mA to 11 mA	
Electrostatic discharge	Human body model ⁽³⁾	A, B, and GND	± 16 kV
		All pins	± 4 kV
	Charged-device model ⁽⁴⁾	All pins charge	± 1 kV
Continuous total power dissipation		See Dissipation Rating Table	
	Electrical Fast Transient/Burst ⁽⁵⁾	A, B, and GND	± 4 kV
T_J	Junction temperature	170°C	

- (1) Stresses beyond those listed under absolute maximum ratings may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated under recommended operating conditions is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.
- (2) All voltage values, except differential I/O bus voltages, are with respect to network ground terminal.
- (3) Tested in accordance with JEDEC Standard 22, Test Method A114-A and IEC 60749-26.
- (4) Tested in accordance with JEDEC Standard 22, Test Method C101.
- (5) Tested in accordance with IEC 61000-4-4.



These devices have limited built-in ESD protection. The leads should be shorted together or the device placed in conductive foam during storage or handling to prevent electrostatic damage to the MOS gates.

RECOMMENDED OPERATING CONDITIONS

over operating free-air temperature range unless otherwise noted

		MIN	NOM	MAX	UNIT
V_{CC}	Supply voltage	3		3.6	V
V_I or V_{IC}	Voltage at any bus terminal (separately or common mode)	-7 ⁽¹⁾		12	
V_{IH}	High-level input voltage	2		V_{CC}	
V_{IL}	Low-level input voltage	0		0.8	
V_{ID}	Differential input voltage	Figure 7		12	
I_{OH}	High-level output current	Driver		-60	mA
		Receiver		-8	
I_{OL}	Low-level output current	Driver		60	mA
		Receiver		8	
R_L	Differential load resistance	54	60		Ω
C_L	Differential load capacitance		50		pF
	Signaling rate	HVD10		32	Mbps
		HVD11		10	
		HVD12		1	
T_J ⁽²⁾	Junction temperature			145	$^{\circ}\text{C}$

(1) The algebraic convention, in which the least positive (most negative) limit is designated as minimum is used in this data sheet.

(2) See thermal characteristics table for information regarding this specification.

DRIVER ELECTRICAL CHARACTERISTICS

over recommended operating conditions unless otherwise noted

PARAMETER		TEST CONDITIONS		MIN	TYP ⁽¹⁾	MAX	UNIT
V_{IK}	Input clamp voltage	$I_I = -18 \text{ mA}$		-1.5			V
$ V_{OD} $	Differential output voltage ⁽²⁾	$I_O = 0$		2		V_{CC}	V
		$R_L = 54 \Omega$, See Figure 1		1.5			
		$V_{\text{test}} = -7 \text{ V to } 12 \text{ V}$, See Figure 2		1.5			
$\Delta V_{OD} $	Change in magnitude of differential output voltage	See Figure 1 and Figure 2		-0.2		0.2	V
$V_{OC(PP)}$	Peak-to-peak common-mode output voltage	See Figure 3			400		mV
$V_{OC(SS)}$	Steady-state common-mode output voltage			1.4		2.5	V
$\Delta V_{OC(SS)}$	Change in steady-state common-mode output voltage			-0.05		0.05	V
I_{OZ}	High-impedance output current	See receiver input currents					
I_I	Input current	D		-100		0	μA
		DE		0		100	
I_{OS}	Short-circuit output current	$-7 \text{ V} \leq V_O \leq 12 \text{ V}$		-250		250	mA
$C_{(OD)}$	Differential output capacitance	$V_{OD} = 0.4 \sin(4E6\pi t) + 0.5 \text{ V}$, DE at 0 V			16		pF
I_{CC}	Supply current	\overline{RE} at V_{CC} , D & DE at V_{CC} , No load	Receiver disabled and driver enabled		9	15.5	mA
		\overline{RE} at V_{CC} , D at V_{CC} , DE at 0 V, No load	Receiver disabled and driver disabled (standby)		1	5	μA
		\overline{RE} at 0 V, D & DE at V_{CC} , No load	Receiver enabled and driver enabled		9	15.5	mA

(1) All typical values are at 25°C and with a 3.3-V supply.

 (2) For $T_A > 85^{\circ}\text{C}$, V_{CC} is $\pm 5\%$.

DRIVER SWITCHING CHARACTERISTICS

over recommended operating conditions unless otherwise noted

PARAMETER		TEST CONDITIONS	MIN	TYP ⁽¹⁾	MAX	UNIT
t _{PLH}	Propagation delay time, low-to-high-level output	HVD10	5	8.5	16	ns
		HVD11	18	25	40	
		HVD12	135	200	300	
t _{PHL}	Propagation delay time, high-to-low-level output	HVD10	5	8.5	16	ns
		HVD11	18	25	40	
		HVD12	135	200	300	
t _r	Differential output signal rise time	HVD10	3	4.5	10	ns
		HVD11	10	20	30	
		HVD12	100	170	300	
t _f	Differential output signal fall time	HVD10	3	4.5	10	ns
		HVD11	10	20	30	
		HVD12	100	170	300	
t _{sk(p)}	Pulse skew (t _{PHL} - t _{PLH})	HVD10			1.5	ns
		HVD11			2.5	
		HVD12			7	
t _{sk(pp)} ⁽²⁾	Part-to-part skew	HVD10			6	ns
		HVD11			11	
		HVD12			100	
t _{PZH}	Propagation delay time, high-impedance-to-high-level output	HVD10			31	ns
		HVD11			55	
		HVD12			300	
t _{PHZ}	Propagation delay time, high-level-to-high-impedance output	HVD10			25	ns
		HVD11			55	
		HVD12			300	
t _{PZL}	Propagation delay time, high-impedance-to-low-level output	HVD10			26	ns
		HVD11			55	
		HVD12			300	
t _{PLZ}	Propagation delay time, low-level-to-high-impedance output	HVD10			26	ns
		HVD11			75	
		HVD12			400	
t _{PZH}	Propagation delay time, standby-to-high-level output	R _L = 110 Ω, \overline{RE} at 3 V, See Figure 5			6	μs
t _{PZL}	Propagation delay time, standby-to-low-level output	R _L = 110 Ω, \overline{RE} at 3 V, See Figure 6			6	μs

(1) All typical values are at 25°C and with a 3.3-V supply.

(2) t_{sk(pp)} is the magnitude of the difference in propagation delay times between any specified terminals of two devices when both devices operate with the same supply voltages, at the same temperature, and have identical packages and test circuits.

RECEIVER ELECTRICAL CHARACTERISTICS

over recommended operating conditions unless otherwise noted

PARAMETER		TEST CONDITIONS	MIN	TYP ⁽¹⁾	MAX	UNIT
V_{IT+}	Positive-going input threshold voltage	$I_O = -8 \text{ mA}$		-0.065	-0.01	V
V_{IT-}	Negative-going input threshold voltage	$I_O = 8 \text{ mA}$	-0.2	-0.1		
V_{hys}	Hysteresis voltage ($V_{IT+} - V_{IT-}$)			35		mV
V_{IK}	Enable-input clamp voltage	$I_I = -18 \text{ mA}$	-1.5			V
V_{OH}	High-level output voltage	$V_{ID} = 200 \text{ mV}$, $I_{OH} = -8 \text{ mA}$, See Figure 7	2.4			V
V_{OL}	Low-level output voltage	$V_{ID} = -200 \text{ mV}$, $I_{OL} = 8 \text{ mA}$, See Figure 7			0.4	V
I_{OZ}	High-impedance-state output current	$V_O = 0$ or V_{CC} , \overline{RE} at V_{CC}	-1		1	μA
I_I	Bus input current	V_A or $V_B = 12 \text{ V}$	HVD11, HVD12, Other input at 0 V	0.05	0.11	mA
		V_A or $V_B = 12 \text{ V}$, $V_{CC} = 0 \text{ V}$		0.06	0.13	
		V_A or $V_B = -7 \text{ V}$		-0.1	-0.05	
		V_A or $V_B = -7 \text{ V}$, $V_{CC} = 0 \text{ V}$		-0.05	-0.04	
		V_A or $V_B = 12 \text{ V}$	HVD10, Other input at 0 V	0.2	0.5	mA
		V_A or $V_B = 12 \text{ V}$, $V_{CC} = 0 \text{ V}$		0.25	0.5	
		V_A or $V_B = -7 \text{ V}$		-0.4	-0.2	
		V_A or $V_B = -7 \text{ V}$, $V_{CC} = 0 \text{ V}$		-0.4	-0.15	
I_{IH}	High-level input current, \overline{RE}	$V_{IH} = 2 \text{ V}$	-30		0	μA
I_{IL}	Low-level input current, \overline{RE}	$V_{IL} = 0.8 \text{ V}$	-30		0	μA
C_{ID}	Differential input capacitance	$V_{ID} = 0.4 \sin(4E6\pi t) + 0.5 \text{ V}$, DE at 0 V		15		pF
I_{CC}	Supply current	\overline{RE} at 0 V, D & DE at 0 V, No load	Receiver enabled and driver disabled	4	8	mA
		\overline{RE} at V_{CC} , D at V_{CC} , DE at 0 V, No load	Receiver disabled and driver disabled (standby)	1	5	μA
		\overline{RE} at 0 V, D & DE at V_{CC} , No load	Receiver enabled and driver enabled	9	15.5	mA

(1) All typical values are at 25°C and with a 3.3-V supply.

RECEIVER SWITCHING CHARACTERISTICS

over recommended operating conditions unless otherwise noted

PARAMETER		TEST CONDITIONS	MIN	TYP ⁽¹⁾	MAX	UNIT
t_{PLH}	Propagation delay time, low-to-high-level output	$V_{ID} = -1.5\text{ V to }1.5\text{ V,}$ $C_L = 15\text{ pF,}$ See Figure 8	12.5	20	25	ns
t_{PHL}	Propagation delay time, high-to-low-level output		12.5	20	25	
t_{PLH}	Propagation delay time, low-to-high-level output		30	55	70	ns
t_{PHL}	Propagation delay time, high-to-low-level output		30	55	70	
$t_{sk(p)}$	Pulse skew ($ t_{PHL} - t_{PLH} $)	HVD10			1.5	ns
		HVD11			4	
		HVD12			4	
$t_{sk(pp)}^{(2)}$	Part-to-part skew	HVD10			8	ns
		HVD11			15	
		HVD12			15	
t_r	Output signal rise time	$C_L = 15\text{ pF,}$ See Figure 8	1	2	5	ns
t_f	Output signal fall time		1	2	5	
$t_{PZH}^{(1)}$	Output enable time to high level	$C_L = 15\text{ pF, DE at }3\text{ V,}$ See Figure 9			15	ns
$t_{PZL}^{(1)}$	Output enable time to low level				15	
t_{PHZ}	Output disable time from high level				20	
t_{PLZ}	Output disable time from low level				15	
$t_{PZH}^{(2)}$	Propagation delay time, standby-to-high-level output	$C_L = 15\text{ pF, DE at }0,$ See Figure 10			6	μs
$t_{PZL}^{(2)}$	Propagation delay time, standby-to-low-level output				6	

- (1) All typical values are at 25°C and with a 3.3-V supply
- (2) $t_{sk(pp)}$ is the magnitude of the difference in propagation delay times between any specified terminals of two devices when both devices operate with the same supply voltages, at the same temperature, and have identical packages and test circuits.

PARAMETER MEASUREMENT INFORMATION

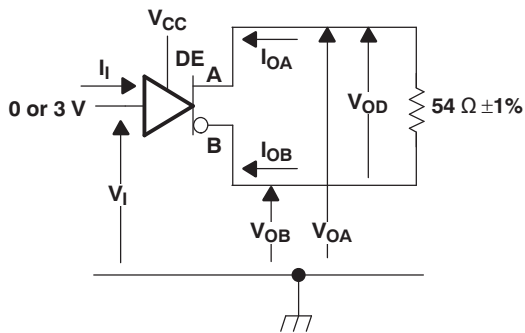


Figure 1. Driver V_{OD} Test Circuit and Voltage and Current Definitions

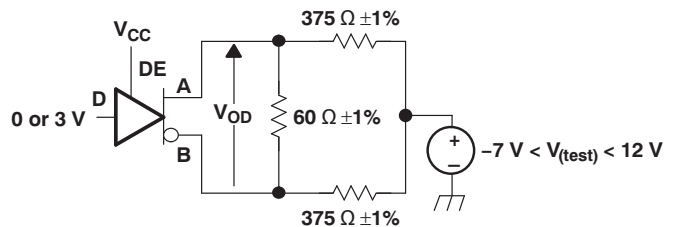
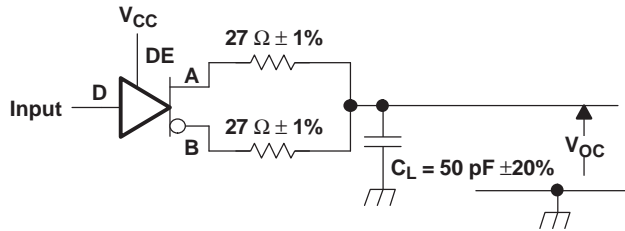


Figure 2. Driver V_{OD} With Common-Mode Loading Test Circuit



C_L Includes Fixture and Instrumentation Capacitance

Input: PRR = 500 kHz, 50% Duty Cycle, $t_r < 6\text{ns}$, $t_f < 6\text{ns}$, $Z_0 = 50 \Omega$

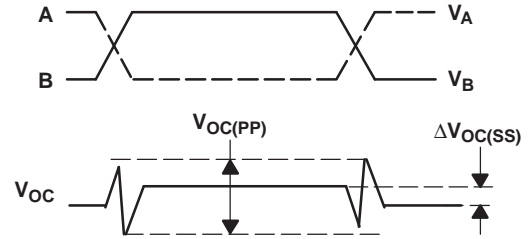
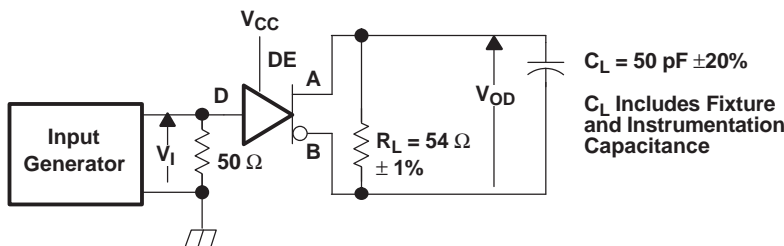


Figure 3. Test Circuit and Definitions for the Driver Common-Mode Output Voltage



$C_L = 50 \text{ pF} \pm 20\%$
 C_L Includes Fixture and Instrumentation Capacitance

Generator: PRR = 500 kHz, 50% Duty Cycle, $t_r < 6 \text{ ns}$, $t_f < 6 \text{ ns}$, $Z_0 = 50 \Omega$

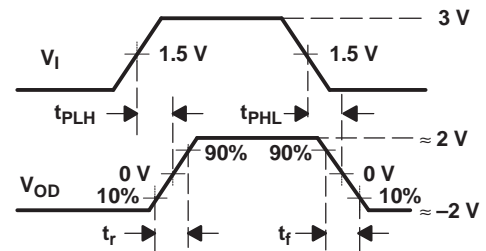
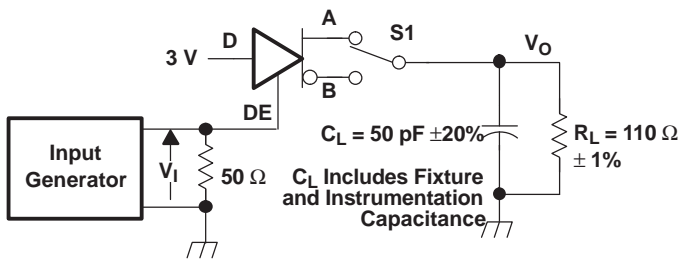


Figure 4. Driver Switching Test Circuit and Voltage Waveforms



$C_L = 50 \text{ pF} \pm 20\%$
 C_L Includes Fixture and Instrumentation Capacitance

Generator: PRR = 500 kHz, 50% Duty Cycle, $t_r < 6 \text{ ns}$, $t_f < 6 \text{ ns}$, $Z_0 = 50 \Omega$

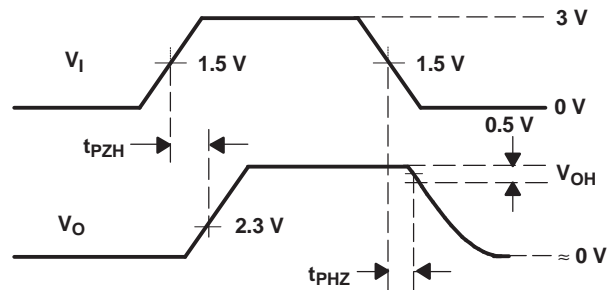
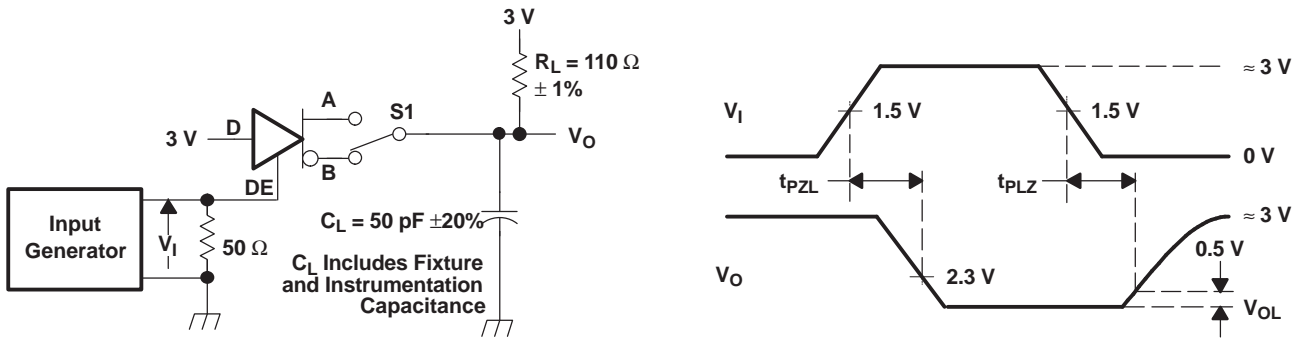


Figure 5. Driver High-Level Enable and Disable Time Test Circuit and Voltage Waveforms



Generator: PRR = 500 kHz, 50% Duty Cycle, $t_r < 6$ ns, $t_f < 6$ ns, $Z_o = 50 \Omega$

Figure 6. Driver Low-Level Output Enable and Disable Time Test Circuit and Voltage Waveforms

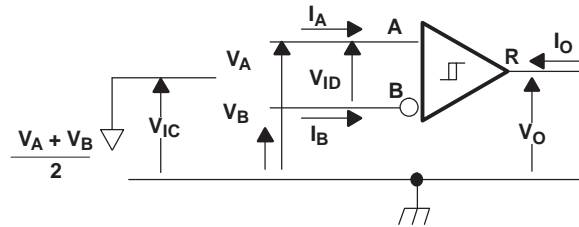
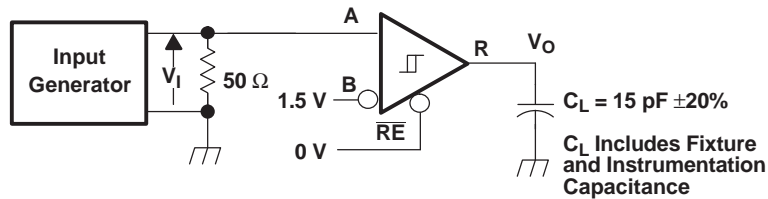


Figure 7. Receiver Voltage and Current Definitions



Generator: PRR = 500 kHz, 50% Duty Cycle, $t_r < 6$ ns, $t_f < 6$ ns, $Z_o = 50 \Omega$

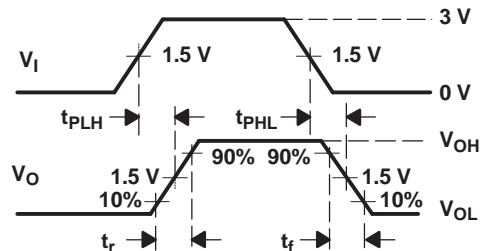


Figure 8. Receiver Switching Test Circuit and Voltage Waveforms

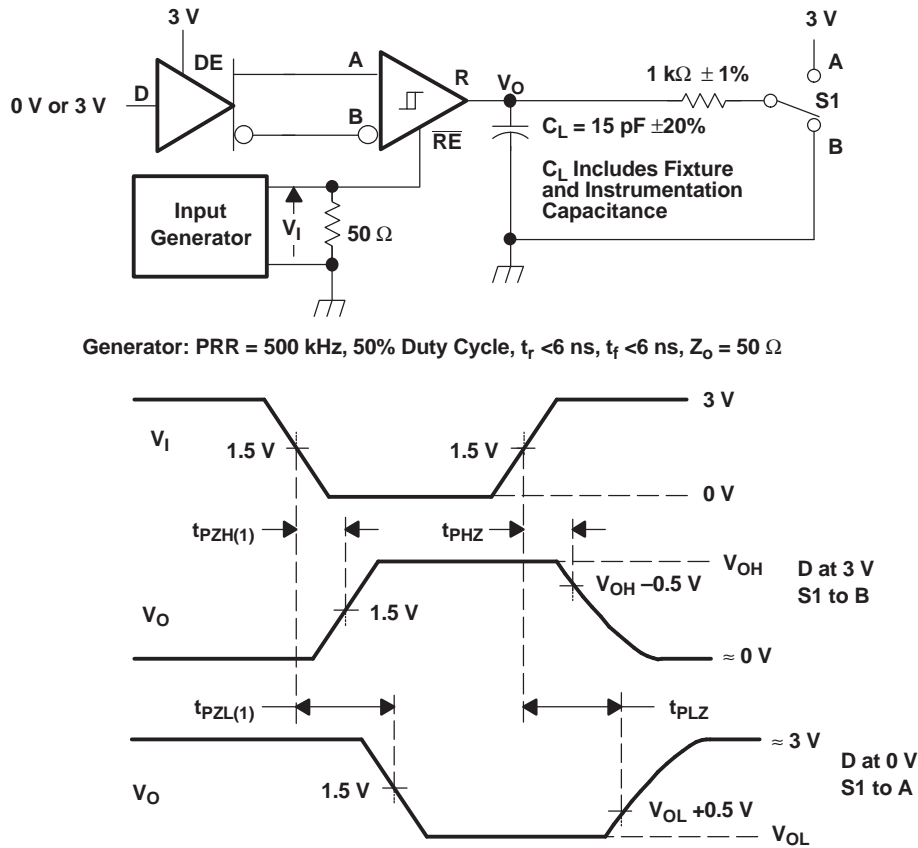


Figure 9. Receiver Enable and Disable Time Test Circuit and Voltage Waveforms With Drivers Enabled

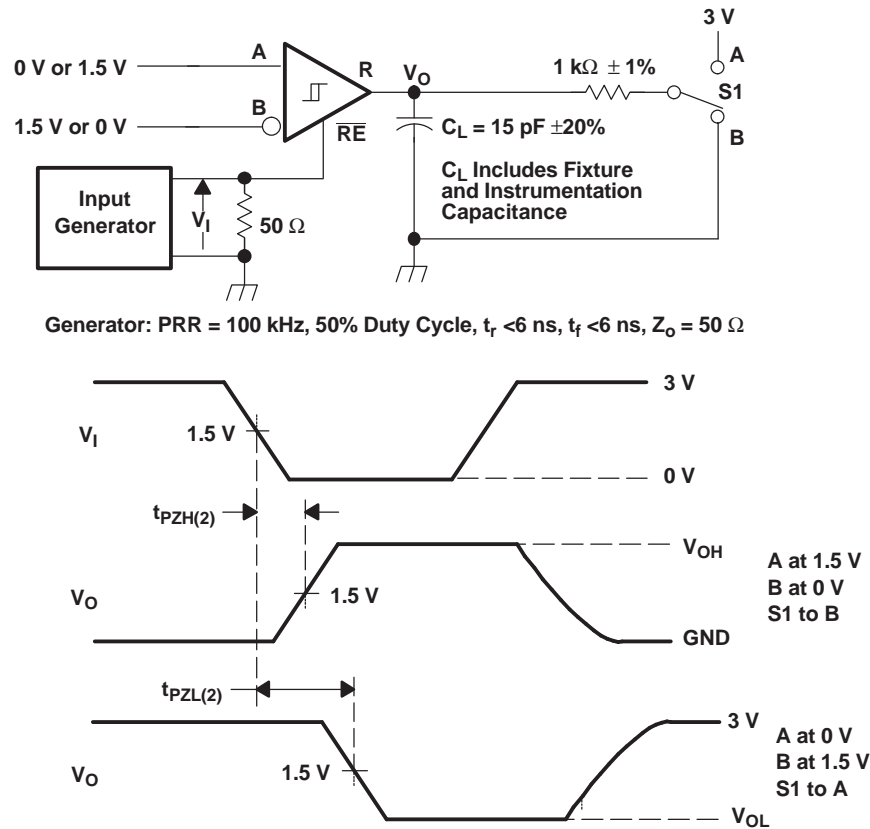
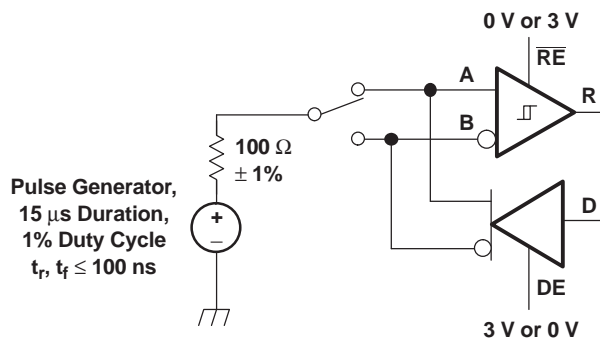


Figure 10. Receiver Enable Time From Standby (Driver Disabled)



NOTE: This test is conducted to test survivability only. Data stability at the R output is not specified.

Figure 11. Test Circuit, Transient Over Voltage Test

PARAMETER MEASUREMENT INFORMATION (continued)
FUNCTION TABLES
Table 1. DRIVER⁽¹⁾

INPUT D	ENABLE DE	OUTPUTS	
		A	B
H	H	H	L
L	H	L	H
X	L	Z	Z
Open	H	H	L

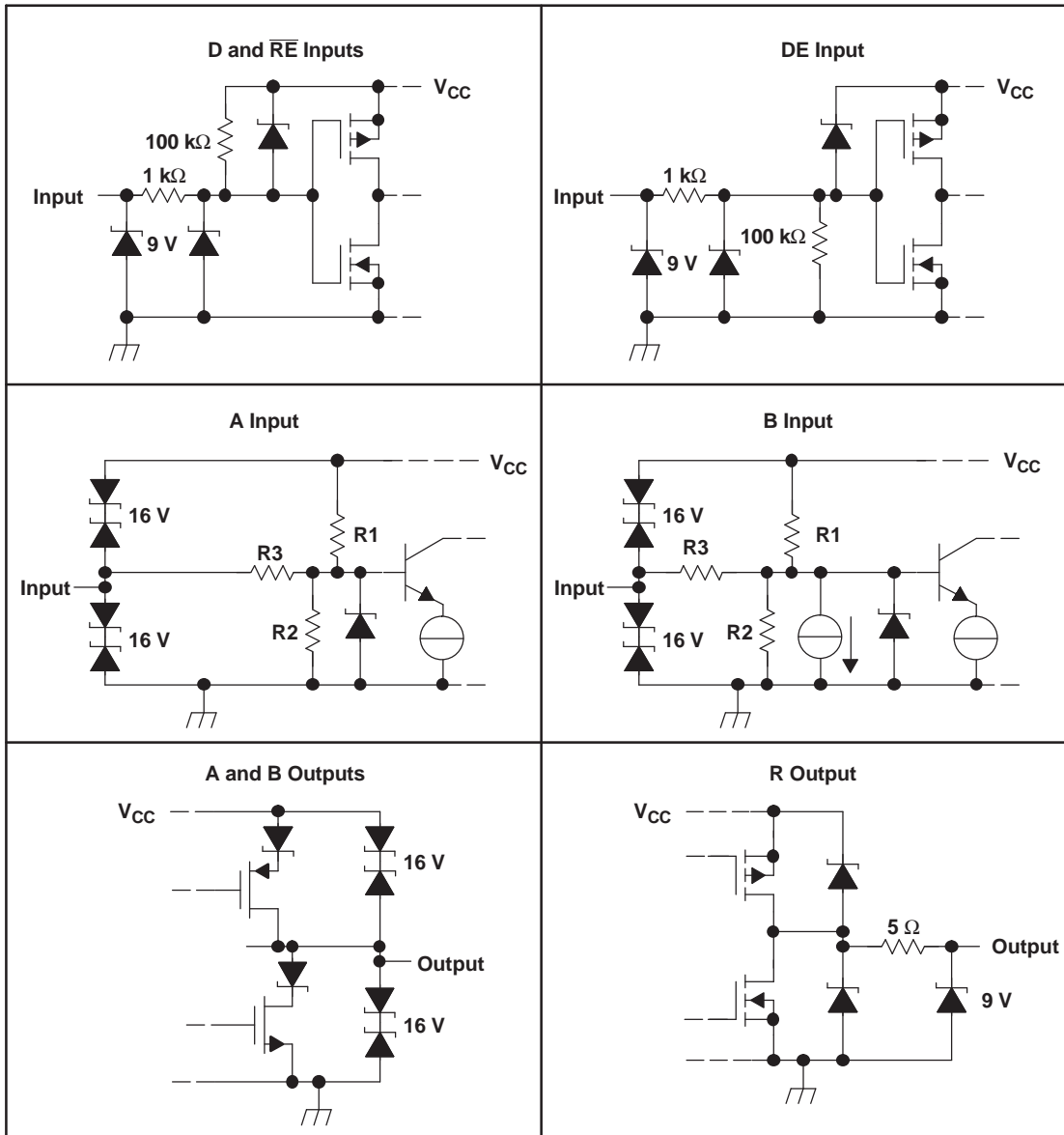
(1) H = high level; L = low level; Z = high impedance; X = irrelevant; ? = indeterminate

Table 2. RECEIVER⁽¹⁾

DIFFERENTIAL INPUTS $V_{ID} = V_A - V_B$	ENABLE \overline{RE}	OUTPUT R
$V_{ID} \leq -0.2 \text{ V}$	L	L
$-0.2 \text{ V} < V_{ID} < -0.01 \text{ V}$	L	?
$-0.01 \text{ V} \leq V_{ID}$	L	H
X	H	Z
Open Circuit	L	H
Short circuit	L	H

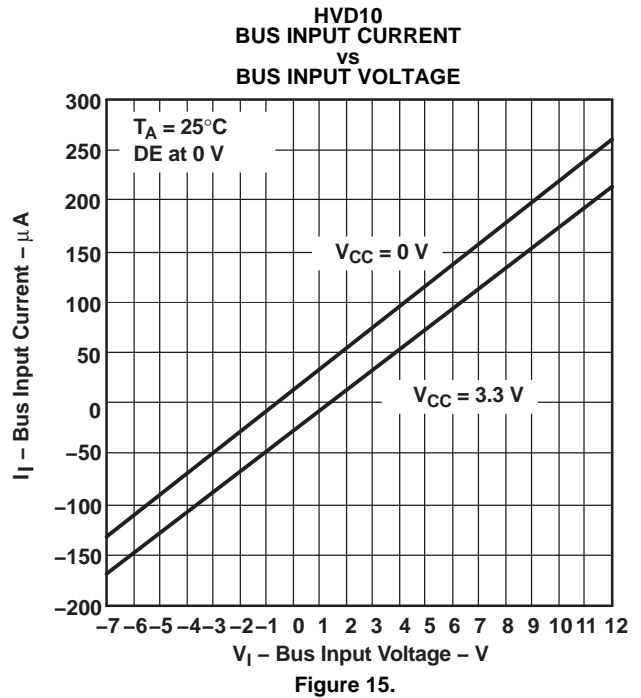
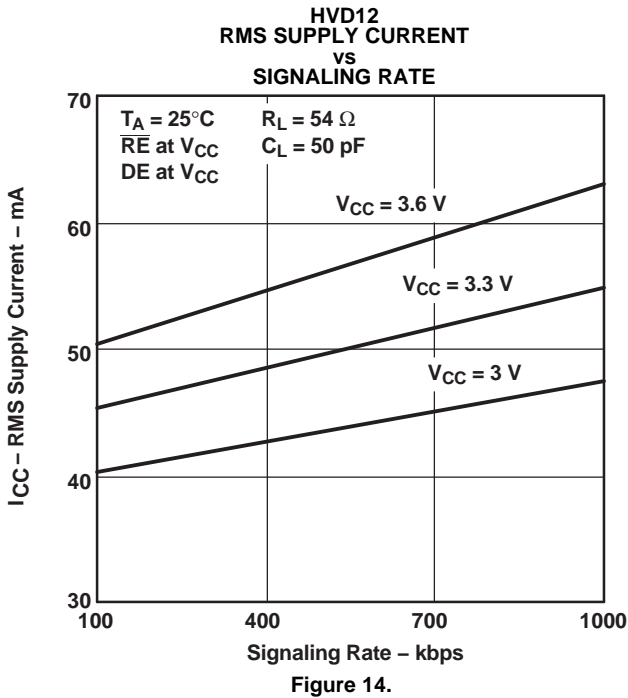
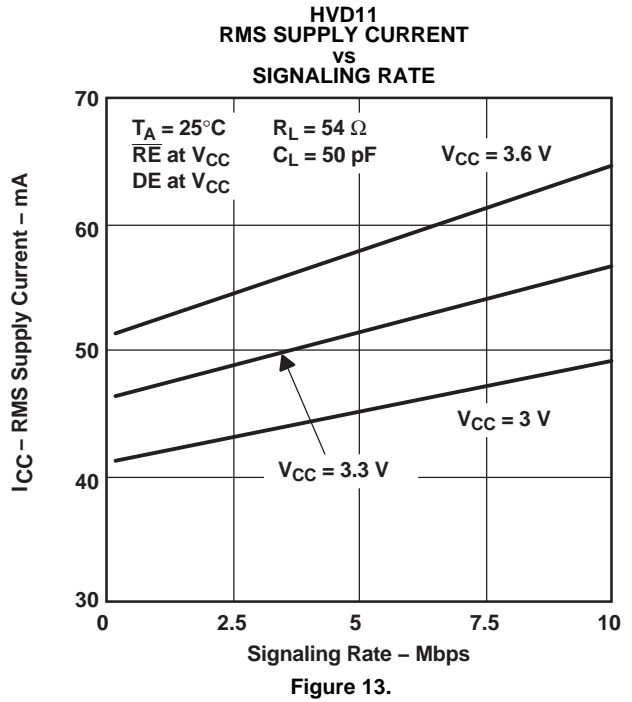
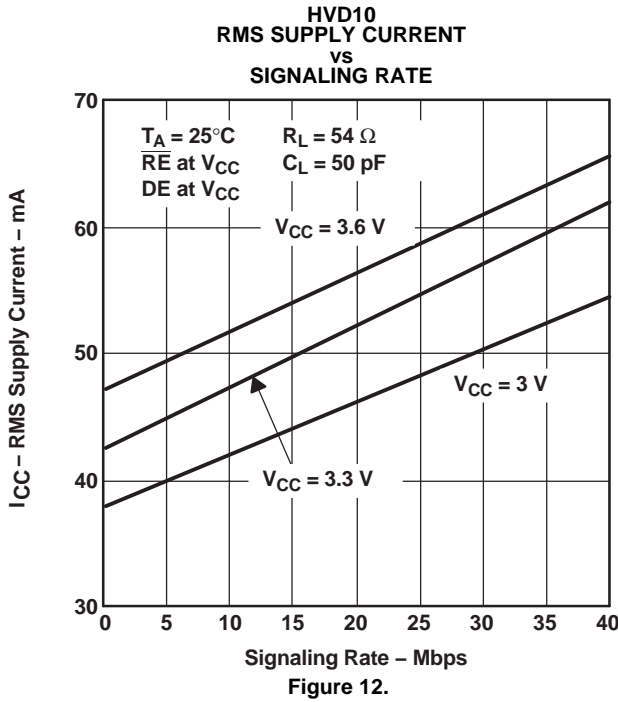
(1) H = high level; L = low level; Z = high impedance; X = irrelevant; ? = indeterminate

EQUIVALENT INPUT AND OUTPUT SCHEMATIC DIAGRAMS

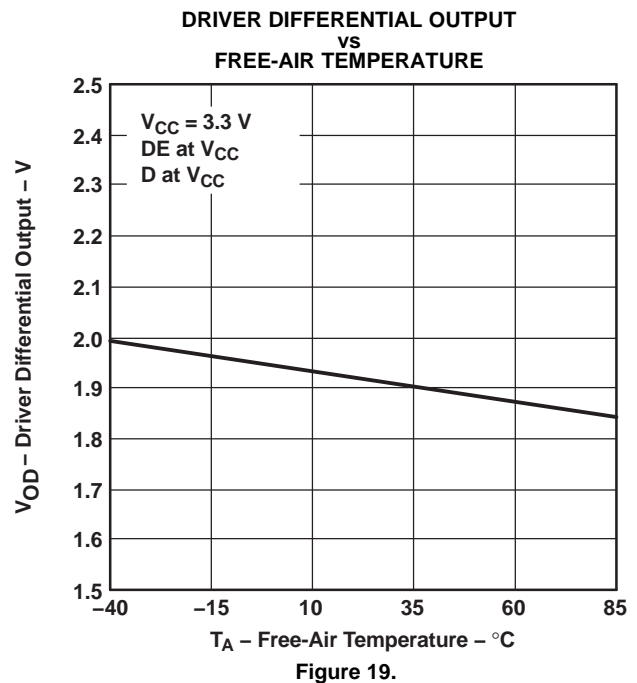
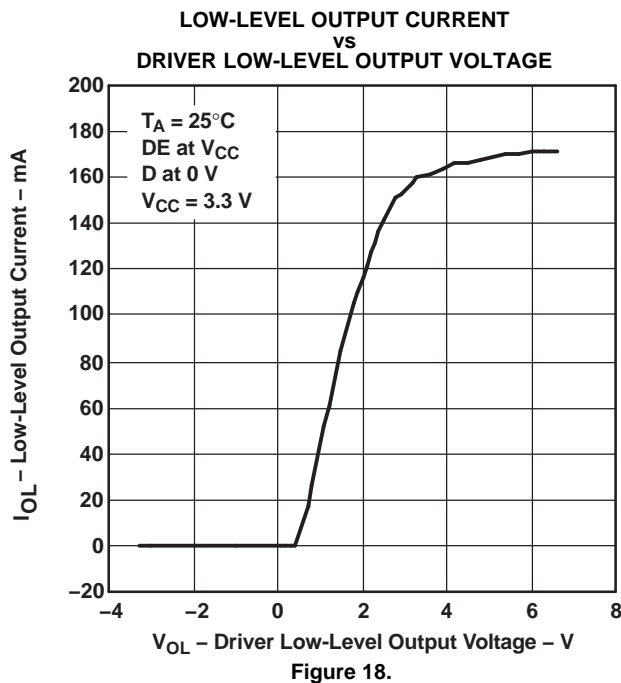
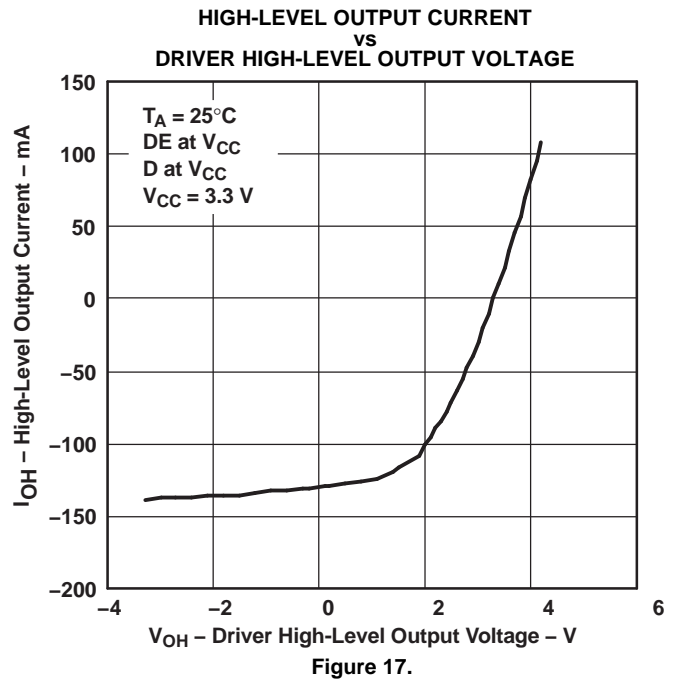
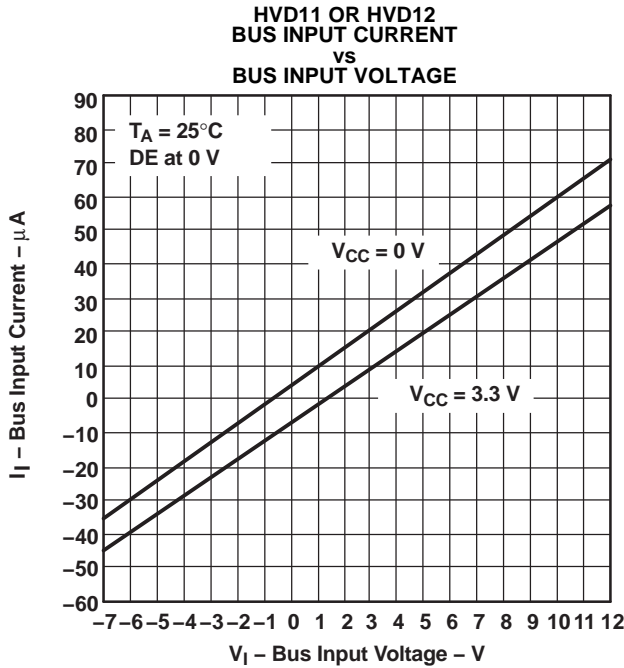


	R1/R2	R3
SN65HVD10	9 kΩ	45 kΩ
SN65HVD11	36 kΩ	180 kΩ
SN65HVD12	36 kΩ	180 kΩ

TYPICAL CHARACTERISTICS



TYPICAL CHARACTERISTICS (continued)



TYPICAL CHARACTERISTICS (continued)

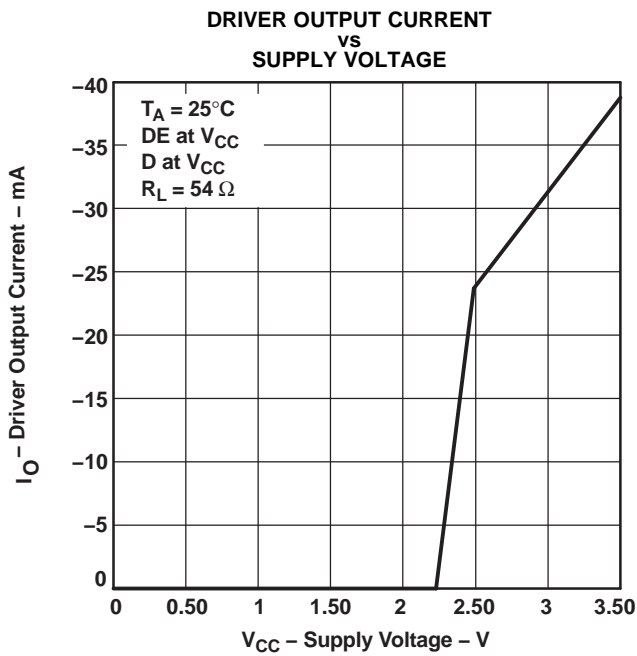


Figure 20.

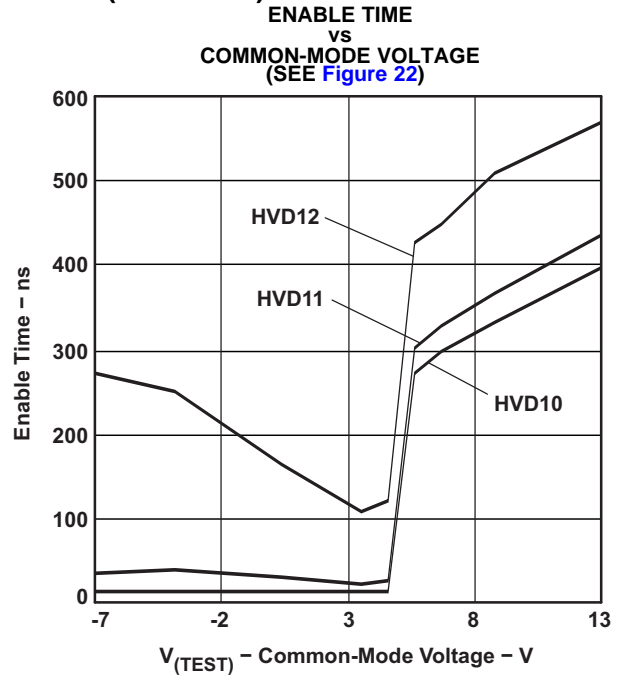


Figure 21.

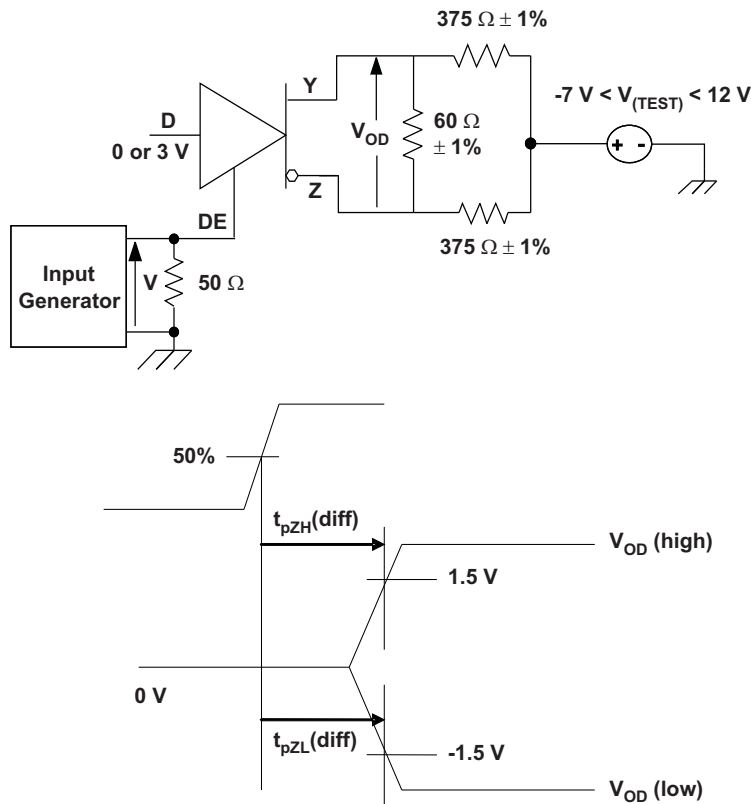
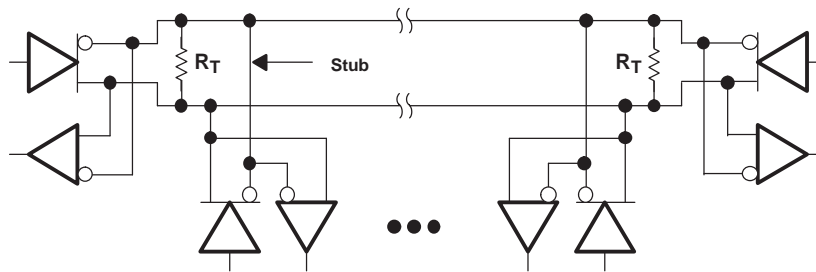


Figure 22. Driver Enable Time From DE to V_{OD}

The time $t_{pZL}(x)$ is the measure from DE to $V_{OD}(x)$. V_{OD} is valid when it is greater than 1.5 V.

APPLICATION INFORMATION



Device	Number of Devices on Bus
HVD10	64
HVD11	256
HVD12	256

NOTE: The line should be terminated at both ends with its characteristic impedance ($R_T = Z_0$). Stub lengths off the main line should be kept as short as possible.

Figure 23. Typical Application Circuit

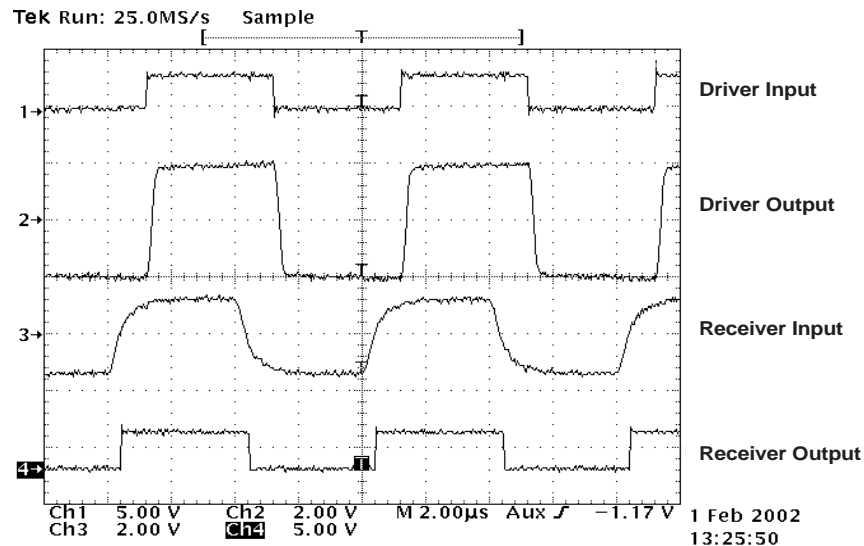


Figure 24. HVD12 Input and Output Through 2000 Feet of Cable

An example application for the HVD12 is illustrated in Figure 23. Two HVD12 transceivers are used to communicate data through a 2000 foot (600 m) length of Commscope 5524 category 5e+ twisted pair cable. The bus is terminated at each end by a 100-Ω resistor, matching the cable characteristic impedance. Figure 24 illustrates operation at a signaling rate of 250 kbps.

LOW-POWER STANDBY MODE

When both the driver and receiver are disabled (DE low and RE high) the device is in standby mode. If the enable inputs are in this state for less than 60 ns, the device does not enter standby mode. This guards against inadvertently entering standby mode during driver/receiver enabling. Only when the enable inputs are held in this state for 300 ns or more, the device is assured to be in standby mode. In this low-power standby mode, most internal circuitry is powered down, and the supply current is typically less than 1 nA. When either the driver or the receiver is re-enabled, the internal circuitry becomes active.

PACKAGE

SOP8

Dimensions In Millimeters					
Symbol :	Min :	Max :	Symbol :	Min :	Max :
A	1.225	1.570	D	0.400	0.950
A1	0.100	0.250	Q	0°	8°
B	4.800	5.100	a	0.420 TYP	
C	5.800	6.250	b	1.270 TYP	
C1	3.800	4.000			

DIP8

Dimensions In Millimeters					
Symbol :	Min :	Max :	Symbol :	Min :	Max :
A	6.100	6.680	L1	3.000	3.600
B	9.000	9.500	a	1.524 TYP	
D	8.400	9.000	b	0.889 TYP	
D1	7.420	7.820	c	0.457 TYP	
E	3.100	3.550	d	2.540 TYP	
L	0.500	0.700			

Important statement:

Huaguan Semiconductor Co,Ltd. reserves the right to change the products and services provided without notice. Customers should obtain the latest relevant information before ordering, and verify the timeliness and accuracy of this information.

Customers are responsible for complying with safety standards and taking safety measures when using our products for system design and machine manufacturing to avoid potential risks that may result in personal injury or property damage.

Our products are not licensed for applications in life support, military, aerospace, etc., so we do not bear the consequences of the application of these products in these fields.

Our documentation is only permitted to be copied without any tampering with the content, so we do not accept any responsibility or liability for the altered documents.

单击下面可查看定价，库存，交付和生命周期等信息

[>>HGSEMI\(华冠\)](#)